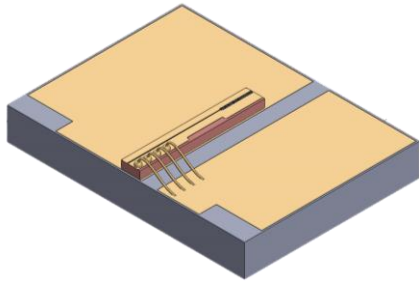
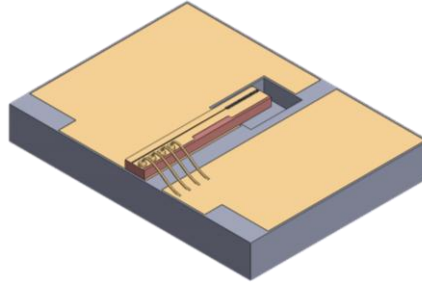


# Specification Sheet | 770.108 nm Series

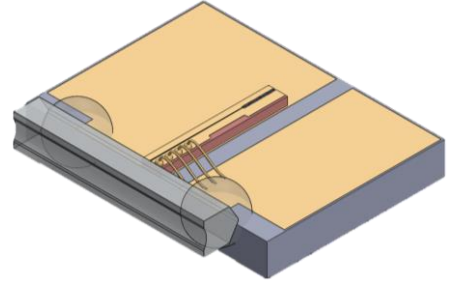
Distributed Bragg Reflector (DBR) Laser Diode



Chip on Submount (CoS)



CoS + Mode-Hop Free (MHF)



CoS + Virtual Point Source (VPS) Lens

## Description

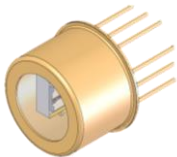
The 770.108 nm DBR Series of high-performance edge-emitting laser diodes are based on Photodigm’s advanced monolithic single-frequency Gallium Arsenide (GaAs) based laser technology. It provides a single spatial mode beam and has passivated facets for reliability. The 770.108 nm Series DBR devices are used in atomic spectroscopy for potassium-based (K) applications. The 770.108 nm Series DBR devices are Spectroscopy Certified; guaranteed to hit the K D1 transition  $\pm 10$  °C from room temperature.

## 770.108 nm DBR Chip on Submount (CoS) Characteristics

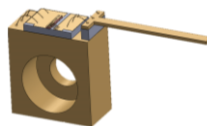
Parameters <sup>1</sup>	Chip Architecture
	High Power
Wavelength, Nominal (nm) <sup>2</sup>	770.108 $\pm$ 0.6
Power Range (mW)	40–100
Operating Current, Max (CW & Pulsed) (mA)	200
Optical Power at Max Operating Current (mW)	100
Slope Efficiency, Nominal (W/A)	0.6
Threshold Current, Nominal (mA)	50

1. Characteristics at  $T_c = 25$  °C unless otherwise specified. Operating outside of these parameters voids warranty.  
 2. Hermetically sealed packages may contain CoS that are  $\pm 1.2$  nm from nominal.

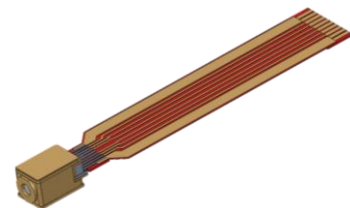
## Available Free-Space Package Add-ons



TO-8



C-Mount



Transmitter Optical Subassembly (TOSA)

# Specification Sheet | 770.108 nm Series

Distributed Bragg Reflector (DBR) Laser Diode

## Specifications

### Laser

Parameter	Unit	Min	Typical	Max
Storage Temperature	°C	0	-	70
Operating Temperature at case	°C	5	-	70
Operating Temperature at laser chip <sup>1</sup>	°C	5	-	45
Laser Series Resistance	Ω	-	2	-
Laser Forward Voltage @ LIV Current	V	-	2	-
Nominal Laser Linewidth @ LIV Current	kHz	-	500	-
Beam Divergence @ FWHM ( $\theta_{  }$ x $\theta_{\perp}$ )	°	-	6 x 28	8 x 32
Side Mode Suppression Ratio (SMSR)	dB	-	-40	-
Polarization Extinction Ratio	dB	-17	-20	-
Laser Polarization	TE			
Mode Structure	Fundamental Mode			
Temperature Tuning Rate	nm/°C	-	0.06	-
Current Tuning Rate	nm/mA	-	0.002	-
Laser Reverse Voltage	V	-	-	0

1. Operation below dew point not recommended without hermetically sealed packaged

### Free-Space Package Add-Ons

Parameter	Unit	Min	Typical	Max
Photodiode Forward Current	mA	-	-	10
Photodiode Reverse Voltage	V	-	-	50
TEC Current (TOSA)	A	-1.1	-	1.1
TEC Voltage (TOSA)	V	-3.0	-	3.0
TEC Current (TO-8)	A	-1.8	-	1.8
TEC Voltage (TO-8)	V	-2.2	-	2.2
Thermistor Resistance	kΩ	-	10	-

### Handling Precautions

These devices are sensitive to ESD. When handling the module, grounded work area and wrist strap must be used. Always store in an antistatic container with all leads shorted together.

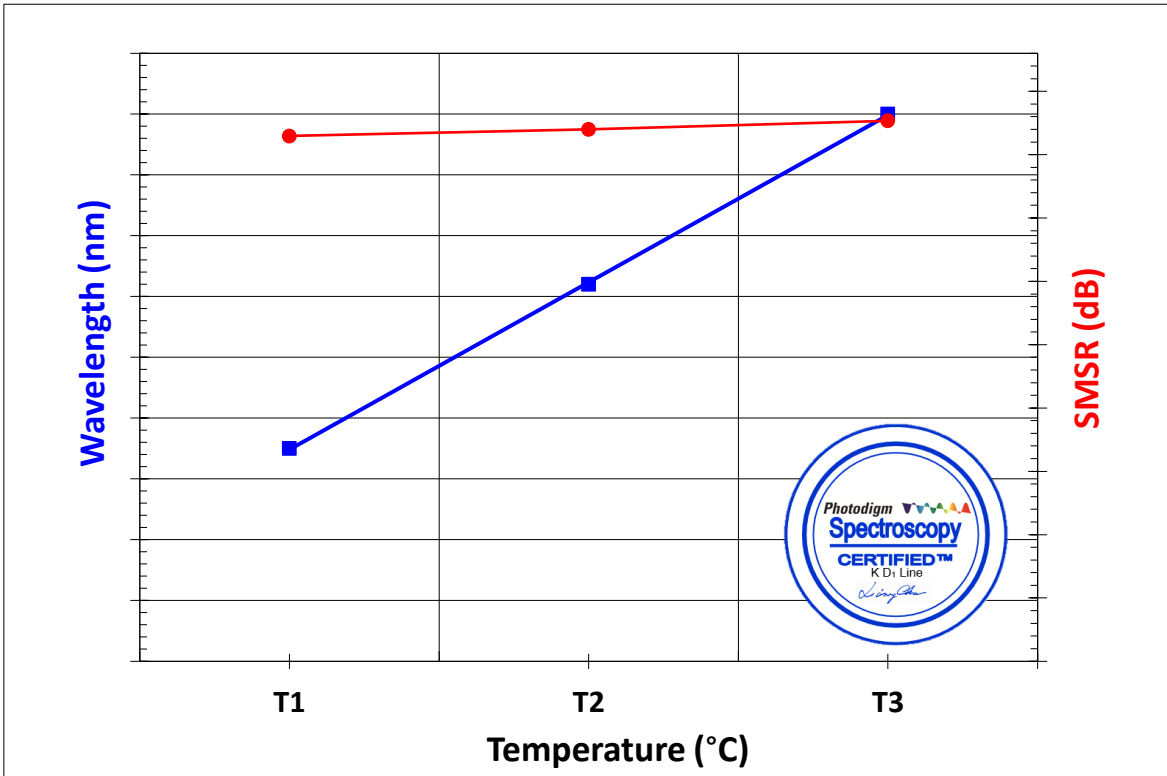


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**Specification Sheet | 770.108 nm Series**

Distributed Bragg Reflector (DBR) Laser Diode

**Air Wavelength Characteristics at Constant Current by Temperature**



**LIV Characteristics by Current**

